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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: 2824
Examiner: To Be Assigned

In Re PATENT APPLICATION of:

Applicant(s): Kun-Hong CHEN)

Serial No.: 10/781,778)

Filed: February 20, 2004)

For: METHOD FOR FABRICATING A LOW)
TEMPERATURE POLYSILICON THIN)
FILM TRANSISTOR)

Atty Ref.: SUND 502)

**INFORMATION
DISCLOSURE
STATEMENT**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This is an information disclosure statement submitted in compliance with the timing requirements of 37 C.F.R. §1.97(b)(3), i.e., prior to a first Office Action on the merits.

Attached is a copy of an English-language article, which was cited by the Taiwanese Patent Office in an Office Action, mailed on June 17, 2004, which was issued in connection with a Taiwanese counterpart application. Any relevance of the article is self-evident. Also, listed for consideration is U.S. patent number US 6,562,670 B2, which was also cited in the above-mentioned Taiwanese Office Action. The article and U.S. patent are listed on the attached Form PTO-1449.

Since this Information Disclosure Statement is being filed before a first Office Action, no certification or fee is required, and the requirements of 37 C.F.R. §§1.97 and 1.98 are deemed to be fully met as to all documents listed. Consideration of the listed documents respectfully is requested.

Should any fee be required, please charge the same to our Deposit Account No. 18-0002 and notify us accordingly.

Respectfully submitted,

November 2, 2004
Date

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RHB:vm

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fee to our Deposit Account
No. 18-0002



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| FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT | | Atty. Docket SUND 502 | | Application No. 10/781,778 | | | |
| | | Applicant Kun-Hong CHEN | | | | | |
| | | Filing Date February 20, 2004 | | Group 2824 | | | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| Examiner Initial | | Document Number | Date | Name | Class | Sub-Class | Filing Date |
| | AA | 6,562,670 | 05/13/03 | SHIH | | | |
| | AB | | | | | | |
| | AC | | | | | | |
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| FOREIGN PATENT DOCUMENTS | | | | | | | |
| | | Document Number | Date | Country | Class | Sub-Class | Translation |
| | AI | | | | | | |
| | AJ | | | | | | |
| | AK | | | | | | |
| | AL | | | | | | |
| OTHER (Including Author, Title, Date, Pertinent Pages, etc.) | | | | | | | |
| | AM | "High-speed Semiconductor Devices" ("Heterostructure Field-Effect Transistors"): International Electron Devices and Materials Symposium; National Sun Yat-sen University, Kaohsiung, Taiwan, R.O.C.; 1988; 3 pages | | | | | |
| | AN | | | | | | |
| Examiner | | | | | Date Considered | | |
| EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant. | | | | | | | |